TOSHIBA GTR Module Silicon N Channel IGBT

# MG75Q2YS50

## High Power Switching Applications Motor Control Applications

• High input impedance

• High speed:  $t_f = 0.3 \mu s \text{ (Max)}$ 

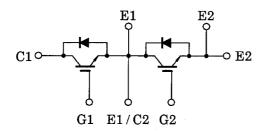
@Iinductive load

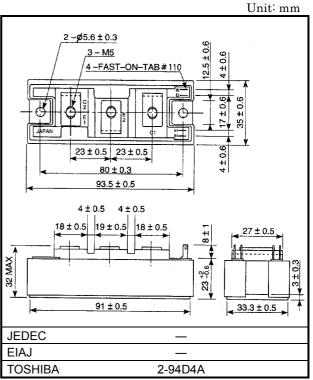
• Low saturation voltage

:  $V_{CE (sat)} = 3.6 \text{ V (Max)}$ 

- Enhancement-mode
- Includes a complete half bridge in one package
- The electrodes are Isolated from case

#### **Equivalent Circuit**





Weight: 202g

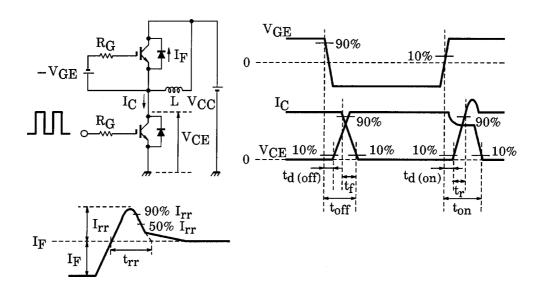
#### **Maximum Ratings (Ta = 25°C)**

| Characteristic                          |     | Symbol                           | Rating               | Unit |  |
|---|-----|----------------------------------|----------------------|------|--|
| Collector-emitter voltage               |     | V <sub>CES</sub>                 | 1200                 | V    |  |
| Gate-emitter voltage                    |     | V <sub>GES</sub>                 | ±20                  | V    |  |
| Collector current                       | DC  | I <sub>C</sub><br>(25°C / 80°C)  | 100 / 75             | Α    |  |
|   | 1ms | I <sub>CP</sub><br>(25°C / 80°C) | 200 / 150            |      |  |
| Forward current                         | DC  | lF                               | 75                   | А    |  |
|   | 1ms | I <sub>FM</sub>                  | 150                  |      |  |
| Collector power dissipation (Tc = 25°C) |     | PC                               | 600                  | W    |  |
| Junction temperature                    |     | Tj                               | 150                  | °C   |  |
| Storage temperature range               |     | T <sub>stg</sub>                 | <b>-</b> 40 ~ 125    | °C   |  |
| Isolation voltage                       |     | V <sub>Isol</sub>                | 2500<br>(AC 1minute) | V    |  |
| Screw torque (Terminal / mounting)      |     | _                                | 3/3                  | N·m  |  |

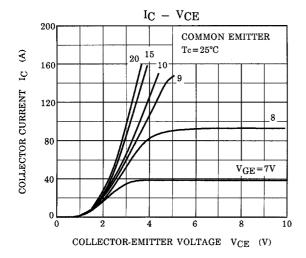
### **Electrical Characteristics (Ta = 25°C)**

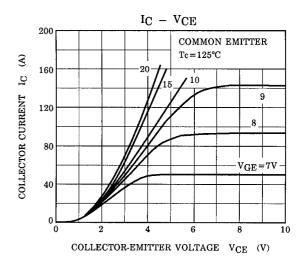
| Characteristic                       |                     | Symbol                | Test Condition   |                        | Min | Тур. | Max  | Unit  |
|--------------------------------------|---------------------|-----------------------|--|------------------------|-----|------|------|-------|
| Gate leakage current                 |                     | I <sub>GES</sub>      | V <sub>GE</sub> = ±20 V, V <sub>CE</sub> = 0   |                        | _   | _    | ±500 | nA    |
| Collector cut-off current            |                     | I <sub>CES</sub>      | V <sub>CE</sub> = 1200 V, V <sub>GE</sub> = 0  |                        | _   | _    | 1.0  | mA    |
| Gate-emitter cut-off voltage         |                     | V <sub>GE (off)</sub> | I <sub>C</sub> = 75 mA, V <sub>CE</sub> = 5 V  |                        | 3.0 | _    | 6.0  | V     |
| Collector-emitter saturation voltage |                     | V <sub>CE</sub> (sat) | I <sub>C</sub> = 75 A,V <sub>GE</sub> = 15 V   | T <sub>j</sub> = 25°C  | _   | 2.8  | 3.6  | V     |
|                                      |                     |                       |  | T <sub>j</sub> = 125°C | _   | 3.1  | 4.0  |       |
| Input capacitance                    | )                   | C <sub>ies</sub>      | V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0,<br>f = 1 MHz                            |                        | _   | 8.5  | _    | nF    |
| Switching time                       | Turn-on delay time  | t <sub>d (on)</sub>   | Inductive load $V_{CC}$ = 600 V $I_{C}$ = 75 A $V_{GE}$ = ±15 V $I_{C}$ = 16 $I_{C}$ |                        | _   | 0.05 | _    |       |
|                                      | Rise-time           | t <sub>r</sub>        |  |                        | _   | 0.05 | _    | μs    |
|                                      | Turn-on time        | t <sub>on</sub>       |  |                        | _   | 0.2  | _    |       |
|                                      | Turn-off delay time | t <sub>d (off)</sub>  |  | (Note 1)               | _   | 0.5  | _    |       |
|                                      | Fall time           | t <sub>f</sub>        |  |                        | _   | 0.1  | 0.3  |       |
|                                      | Turn-off time       | t <sub>off</sub>      |  |                        | _   | 0.6  | _    |       |
| Forward voltage                      |                     | V <sub>F</sub>        | I <sub>F</sub> = 75 A, V <sub>GE</sub> = 0   |                        | _   | 2.4  | 3.5  | V     |
| Reverse recovery time                |                     | t <sub>rr</sub>       | I <sub>F</sub> = 75 A, V <sub>GE</sub> = -10 V<br>di / dt = 700 A / μs (Note 1)      |                        | _   | 0.1  | 0.25 | μs    |
| Thermal resistance                   |                     | R <sub>th (j-c)</sub> | Transistor stage   |                        | _   | _    | 0.2  | °C/W  |
|                                      |                     |                       | Diode stage  | _                      | _   | _    | 0.47 | C / W |

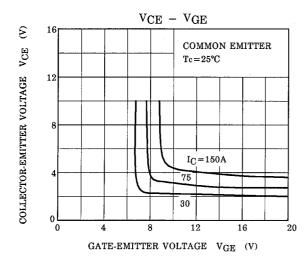
Note 1: Switching time and reverse recovery time test circuit & timing chart

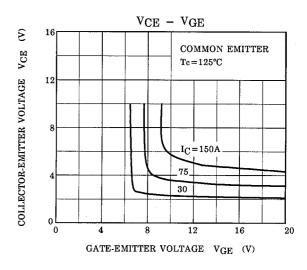


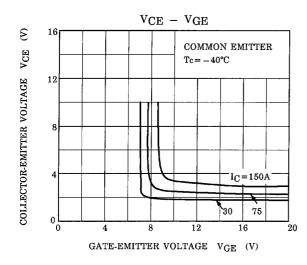
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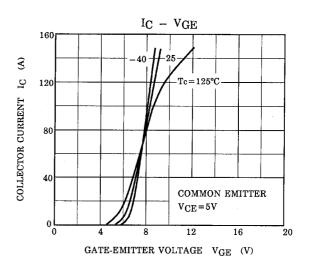




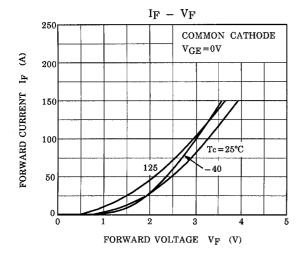


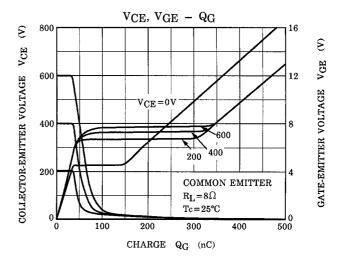


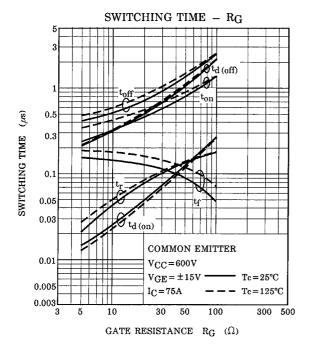


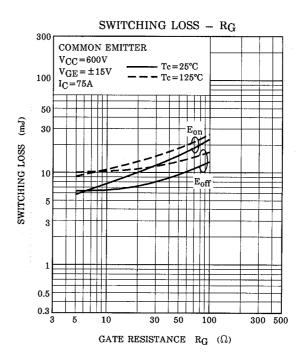


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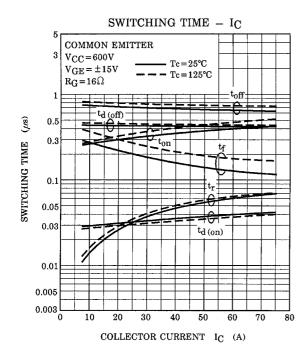


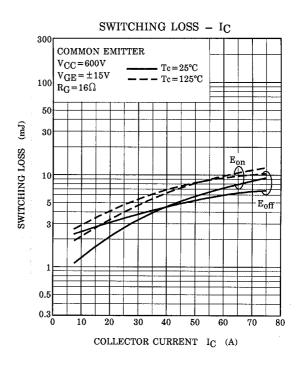


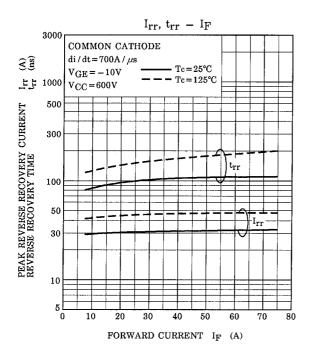


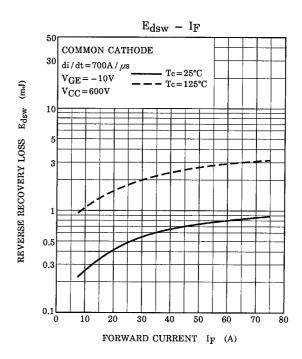


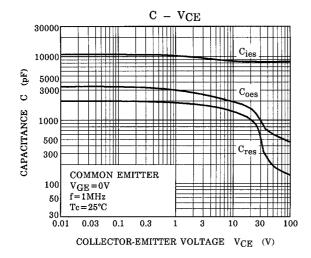
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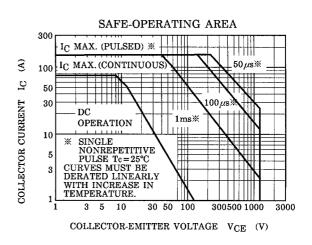


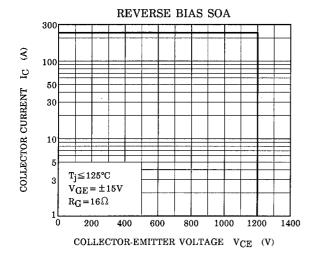


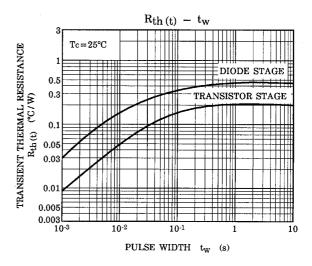


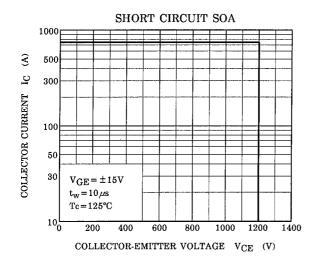












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